



Micro Commercial Components
 21201 Itasca Street Chatsworth
 CA 91311
 Phone: (818) 701-4933
 Fax: (818) 701-4939

2SC2336

NPN Silicon Power Transistors

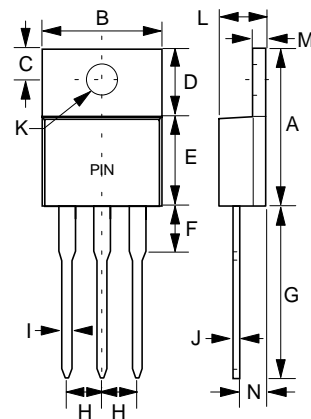
Features

- With TO-220 package
- Power amplifier applications

Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CE0}	Collector-Emmitter Voltage	180	V
V_{CB0}	Collector-Base Voltage	180	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current	1.5	A
P_C	Collector power dissipation	25	W
T_J	Junction Temperature	-55 to +150	$^{\circ}C$
T_{STG}	Storage Temperature	-55 to +150	$^{\circ}C$

TO-220



Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
--------	-----------	-----	-----	-------

OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emmitter Breakdown Voltage ($I_C=50mA$, $I_B=0$)	180	---	Vdc
I_{CBO}	Collector-Base Cutoff Current ($V_{CB}=150V$, $I_E=0$)	---	1.0	μA
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB}=5.0V$, $I_C=0$)	---	1.0	μA

ON CHARACTERISTICS

h_{FE}	Forward Current Transfer ratio ($I_C=0.15A$, $V_{CE}=5.0V$)	60	320	---
$V_{CE(sat)}$	Collector-Emmitter Saturation Voltage ($I_C=0.5A$, $I_B=0.05A$)	---	1.0	Vdc
$V_{BE(sat)}$	Base-Emmitter Saturation Voltage ($I_C=0.5A$, $I_B=0.05A$)	---	1.5	Vdc

DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.560	.625	14.22	15.88	
B	.380	.420	9.65	10.67	
C	.100	.135	2.54	3.43	
D	.230	.270	5.84	6.86	
E	.380	.420	9.65	10.67	
F	-----	.250	-----	6.35	
G	.500	.580	12.70	14.73	
H	.090	.110	2.29	2.79	
I	.020	.045	0.51	1.14	
J	.012	.025	0.30	0.64	
K	.139	.161	3.53	4.09	∅
L	.140	.190	3.56	4.83	
M	.045	.055	1.14	1.40	
N	.080	.115	2.03	2.92	